

IN THE CLAIMS

1 (Original). A method comprising:

forming a tapered electrode for a phase-change memory cell; and
forming a trench using the tapered electrode as a mask.

2 (Original). The method of claim 1 including covering said tapered electrode with an insulator.

3 (Currently Amended). The method of claim 1 including covering said electrode with an insulator and forming a pair of trenches using said electrode as a mask. ~~forming a pair of tapered electrodes for a pair of adjacent phase-change memory cells, covering the electrodes with an insulator and forming a trench between the covered tapered electrodes as a mask.~~

4 (Original). The method of claim 1 including self-aligning the trench to the tapered electrode.

5 (Original). The method of claim 1 including forming a tapered electrode by isotropically etching.

Claim 6 (Canceled).

7 (Original). The method of claim 6 including forming a plurality of layers of different doping levels.

8 (Original). The method of claim 7 including forming said layers by ion implantation.

9 (Original). The method of claim 7 including etching said layers using the same isotropic etch used to form said tapered electrode.

10 (Original). The method of claim 9 including forming a tapered substrate portion below said tapered electrode.

11 (Original). The method of claim 10 including forming a conical-shaped substrate portion covered by said tapered electrode.

12 (Original). The method of claim 10 including covering said tapered substrate portion with an insulator and anisotropic etching said covered tapered substrate portion.